

Method and Apparatus for Plating Semiconductor Wafers

ABSTRACT OF THE DISCLOSURE

First and second electrodes are disposed at first and second locations, respectively,
5 proximate to a periphery of a wafer support, wherein the first and second location are substantially opposed to each other relative to the wafer support. Each of the first and second electrodes can be moved to electrically connect with and disconnect from a wafer held by the wafer support. An anode is disposed over and proximate to the wafer such that a meniscus of electroplating solution is maintained between the anode and the wafer. As
10 the anode moves over the wafer from the first location to the second location, an electric current is applied through the meniscus between the anode and the wafer. Also, as the anode is moved over the wafer, the first and second electrodes are controlled to connect with the wafer while ensuring that the anode does not pass over an electrode that is connected.

Figure 1A